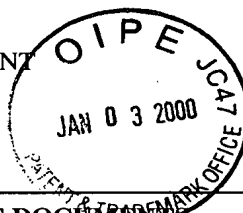


37 CFR 1.501
 INFORMATION DISCLOSURE STATEMENT
 IN A PATENT
 (use several sheets if necessary)



Docket No. P97,0027	Serial No. 08/818,239
Applicant Hiroshi Tayanaka	
Filing Date March 14, 1997	Group Art Unit 2813

U.S. PATENT DOCUMENTS

Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If appropriate
<i>KC</i>	AA	4,727,047	02-23-88	Bozler, et al.	—	—	
<i>KC</i>	AB	5,854,123	12-29-98	Sato, et al.	—	—	
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FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
<i>KC</i>	AL	JP62-279625	12-04-87	Japan	—	—	Abstract	X
	AM							
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OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>KC</i>	AT	V. Labunov, et al., "Heat Treatment Effect on Porous Silicon", Thin Solid Films, Vol. 137, pp. 123-134, 1986
<i>KC</i>	AU	N. Sato, et al., "Epitaxial Growth on Porous Si for a New Bond and Etch-back SOI", The Electrochemical Society, Spring Meeting, May 22-27, 1994, Extended Abstracts, Vol. 94-1, Abstract No. 443, pp. 705-706
	AV	"Crystalline Silicon and Doping", Maruzen Kabushiki Kaisha Publisher, 1986
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Examiner *KC Clinton*Date Considered *6/5/2000*

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

no
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